

# Xuan Zhang

## List of Publications by Citations

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23  
papers

229  
citations

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g-index

24  
ext. papers

254  
ext. citations

1.9  
avg, IF

2.87  
L-index

#	Paper	IF	Citations
23	Photoluminescence of Frank-type defects on the basal plane in 4H-SiC epilayers. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 172107	3.4	52
22	Recent advances in 4H-SiC epitaxy for high-voltage power devices. <i>Materials Science in Semiconductor Processing</i> , <b>2018</b> , 78, 2-12	4.3	35
21	Cross-sectional structure of carrot defects in 4H-SiC epilayers. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 5209-5214	3.4	32
20	Conversion of basal plane dislocations to threading edge dislocations in 4H-SiC epilayers by high temperature annealing. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 123512	2.5	21
19	Correlation between Thermal Stress and Formation of Interfacial Dislocations during 4H-SiC Epitaxy and Thermal Annealing. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 306-309	0.4	21
18	Critical Conditions of Misfit Dislocation Formation in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 313-318	0.4	16
17	Irradiation-Induced Nanoprecipitation in Ni-W Alloys. <i>Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science</i> , <b>2015</b> , 46, 1046-1061	2.3	9
16	Spheroid 3C inclusions in 8° off-axis 4H-SiC epilayers grown by chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 123529	2.5	9
15	Effects of Nitrogen Doping on the Morphology of Basal Plane Dislocations in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 335-338	0.4	7
14	Nondestructive dislocation delineation using topographically enhanced imaging of surface morphologies in 4H-SiC epitaxial layers. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 074904	2.5	6
13	Photoluminescence Imaging and Wavelength Analysis of Basal Plane Frank-Type Defects in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2012</b> , 725, 15-18	0.4	5
12	Non-equilibrium Grain Boundary Wetting in Cu <sub>3</sub> Ag Alloys Containing W Nanoparticles. <i>Materials Research Letters</i> , <b>2016</b> , 4, 22-26	7.4	3
11	Dependence of spontaneous polarization on stacking sequence in SiC revealed by local Schottky barrier height variations over a partially formed 8H-SiC layer on a 4H-SiC substrate. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 252102	3.4	3
10	2.0 kV/2.1 m <sup>2</sup> Lateral p-GaN/AlGaN/GaN Hybrid Anode Diodes with Hydrogen Plasma Treatment. <i>IEEE Electron Device Letters</i> , <b>2022</b> , 1-1	4.4	3
9	Silicon carbide and graphene based UV-IR dual-color detector. <i>Optoelectronics Letters</i> , <b>2019</b> , 15, 170-173	0.7	2
8	Studies of deep-submicrometer ultranarrow-track recording by composite Simulation models. <i>IEEE Transactions on Magnetics</i> , <b>2004</b> , 40, 1958-1962	2	2
7	Conversion of Basal Plane Dislocations to Threading Edge Dislocations by Annealing 4H-SiC Epilayers at High Temperatures. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 601-604	0.4	1

6	Investigation of Photoluminescence Emission of Basal Plane Frank-Type Defects in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 310-313	0.4	1
5	Basal Plane Dislocations in 4H-SiC Epilayers with Different Dopings. <i>Materials Science Forum</i> , <b>2012</b> , 725, 27-30	0.4	1
4	Microstructure of Interfacial Basal Plane Dislocations in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2019</b> , 954, 77-81	0.4	
3	Extension, Closure and Conversion of In-Grown Stacking Faults in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2018</b> , 924, 155-159	0.4	
2	Elimination of Silicon Droplets Formation during 4H-SiC Epitaxial Growth by Chloride-Based CVD in a Vertical Hot-Wall Reactor. <i>Materials Science Forum</i> , 1014, 3-7	0.4	
1	Identification of the Structures and Sources of Shockley-Type In-Grown Stacking Faults in 4H-SiC Epilayers. <i>Crystal Research and Technology</i> , <b>2018</b> , 53, 1700234	1.3	